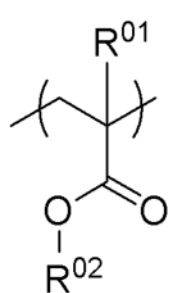


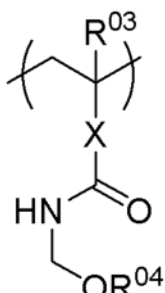
**TITLE OF INVENTION: COMPOSITION FOR FORMING RESIST UNDERLAYER
FILM, PATTERNING PROCESS, AND RESIST UNDERLAYER FILM
FORMATION PROCESS**

ABSTRACT

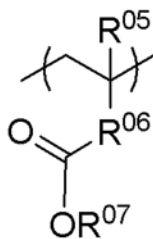
An object of the present invention is to provide a composition for forming a resist underlayer film, which serves as an antireflective film and which has excellent resistance to alkaline hydrogen peroxide water and favorable filling/planarization characteristics and dry etching characteristics, as well as a patterning process and a resist underlayer film formation process each using the composition. A composition for forming a resist underlayer film, the composition including: (A) a polymer compound having a structural unit (a1) represented by the following formula (A-1) and at least one structural unit (a2) selected from structural units represented by the following formulae (A-2) to (A-4); (B) a crosslinking agent represented by the following formula (B-1); and (C) an organic solvent.



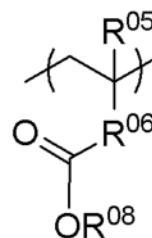
(A-1)



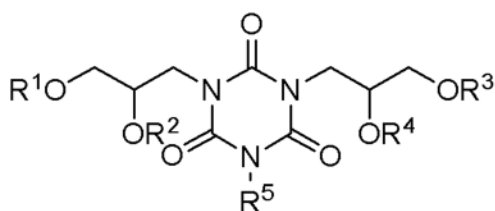
(A-2)



(A-3)



(A-4)



(B-1)

[Fig. 1 (A) to 1(F)]